

C through the insulating film in contact with the metal base at the openings in the insulating film and in contact with the insulating film where there are no openings in the insulating film.

IN THE CLAIMS:

Please amend Claim 2, as follows:

2. (Amended) A method for fabricating a wiring substrate comprising the steps of:

forming an insulating film on a metal base having openings on the metal base at positions corresponding to metal bumps to be formed later;

forming at least one layer of wiring on the base made of a metal through the insulating film, the layer of wiring having a wiring film formed thereon by electroplating; and

selectively etching the base.

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Please add the following new claims:

C3 15. (NEW) The method of claim 2 wherein the insulating film is an insulating resin.

16. (NEW) The method of claim 2 wherein the insulating film is a photosensitive resin.

17. (NEW) The method of claim 2 wherein the insulating film is a liquid photosensitive polyamide.

18. (NEW) The method of claim 2 wherein the insulating film is an epoxy.

19. (NEW) The method of claim 2 wherein the wiring layer is made of copper.

20. (NEW) The method of claim 2 wherein the wiring film is a film on the under side of the wiring layer between the wiring layer and the metal base.

21. (NEW) The method of claim 2 wherein the wiring film is a conductive layer selected from the group consisting of Ni-P and Ni.

22. (NEW) The method of claim 2 wherein the base is made of copper.

23. (NEW) The method of claim 2 wherein the wiring layer formed through the insulating film is in contact with the metal base.

24. (NEW) The method of claim 2 wherein the wiring layer formed through the insulating film is in contact with the metal base at the openings in the insulating film and in contact with the insulating film where there are no openings in the insulating film.

25. (NEW) The method of claim 2 wherein the wiring layer is formed in the area of the openings on the insulating film so as to be formed through the film in contact with the base.

26. (NEW) The method of claim 2 wherein the insulating layer can function as an etching stopper.

27. (NEW) The method of claim 2 wherein the wiring film can function as an etching stopper.

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Concluded